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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, IR, LCD, POR, PWM, WDT
Number of I/O	41
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	1K x 8
RAM Size	2K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 25x12b; D/A 1x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8l152c6t6

List of figures

The medium-density STM8L15x microcontroller family is suitable for a wide range of applications:

- Medical and hand-held equipment
- Application control and user interface
- PC peripherals, gaming, GPS and sport equipment
- Alarm systems, wired and wireless sensors

3.6 LCD (Liquid crystal display)

The liquid crystal display drives up to 4 common terminals and up to 28 segment terminals to drive up to 112 pixels.

- Internal step-up converter to guarantee contrast control whatever V_{DD}.
- Static 1/2, 1/3, 1/4 duty supported.
- Static 1/2, 1/3 bias supported.
- Phase inversion to reduce power consumption and EMI.
- Up to 4 pixels which can programmed to blink.
- The LCD controller can operate in Halt mode.

Note: Unnecessary segments and common pins can be used as general I/O pins.

3.7 Memories

The medium-density STM8L151x4/6 and STM8L152x4/6 devices have the following main features:

- Up to 2 Kbyte of RAM
- The non-volatile memory is divided into three arrays:
  - Up to 32 Kbyte of medium-density embedded Flash program memory
  - 1 Kbyte of data EEPROM
  - Option bytes.

The EEPROM embeds the error correction code (ECC) feature. It supports the read-while-write (RWW): it is possible to execute the code from the program matrix while programming/erasing the data matrix.

The option byte protects part of the Flash program memory from write and readout piracy.

3.8 DMA

A 4-channel direct memory access controller (DMA1) offers a memory-to-memory and peripherals-from/to-memory transfer capability. The 4 channels are shared between the following IPs with DMA capability: ADC1, DAC, I2C1, SPI1, USART1, the four Timers.

3.9 Analog-to-digital converter

- 12-bit analog-to-digital converter (ADC1) with 25 channels (including 1 fast channel), temperature sensor and internal reference voltage
- Conversion time down to 1 µs with f_{SYSCLK}= 16 MHz
- Programmable resolution
- Programmable sampling time
- Single and continuous mode of conversion
- Scan capability: automatic conversion performed on a selected group of analog inputs
- Analog watchdog
- Triggered by timer

have a fixed value: 0x3.

4. Refer to *Table 9* for an overview of hardware register mapping, to *Table 8* for details on I/O port hardware registers, and to *Table 10* for information on CPU/SWIM/debug module controller registers.

Table 6. Flash and RAM boundary addresses

Memory area	Size	Start address	End address
RAM	2 Kbyte	0x00 0000	0x00 07FF
Flash program memory	16 Kbyte	0x00 8000	0x00 BFFF
	32 Kbyte	0x00 8000	0x00 FFFF

5.2 Register map

Table 7. Factory conversion registers

Address	Block	Register label	Register name	Reset status
0x00 4910	-	VREFINT_Factory_CONV(1)	Internal reference voltage factory conversion	0xXX
0x00 4911	-	TS_Factory_CONV_V90(2)	Temperature sensor output voltage	0xXX

1. The VREFINT_Factory_CONV byte represents the 8 LSB of the result of the VREFINT 12-bit ADC conversion performed in factory. The MSB have a fixed value: 0x6.
2. The TS_Factory_CONV_V90 byte represents the 8 LSB of the result of the V90 12-bit ADC conversion performed in factory. The 2 MSB have a fixed value: 0x3.

Table 8. I/O port hardware register map

Address	Block	Register label	Register name	Reset status
0x00 5000	Port A	PA_ODR	Port A data output latch register	0x00
0x00 5001		PA_IDR	Port A input pin value register	0xXX
0x00 5002		PA_DDR	Port A data direction register	0x00
0x00 5003		PA_CR1	Port A control register 1	0x01
0x00 5004		PA_CR2	Port A control register 2	0x00
0x00 5005	Port B	PB_ODR	Port B data output latch register	0x00
0x00 5006		PB_IDR	Port B input pin value register	0xXX
0x00 5007		PB_DDR	Port B data direction register	0x00
0x00 5008		PB_CR1	Port B control register 1	0x00
0x00 5009		PB_CR2	Port B control register 2	0x00

Table 9. General hardware register map (continued)

Address	Block	Register label	Register name	Reset status
0x00 534E	ADC1	ADC1_TRIGR1	ADC1 trigger disable 1	0x00
0x00 534F		ADC1_TRIGR2	ADC1 trigger disable 2	0x00
0x00 5350		ADC1_TRIGR3	ADC1 trigger disable 3	0x00
0x00 5351		ADC1_TRIGR4	ADC1 trigger disable 4	0x00
0x00 5352 to 0x00 537F	Reserved area (46 bytes)			
0x00 5380	DAC	DAC_CR1	DAC control register 1	0x00
0x00 5381		DAC_CR2	DAC control register 2	0x00
0x00 5382 to 0x00 5383		Reserved area (2 bytes)		
0x00 5384		DAC_SWTRIGR	DAC software trigger register	0x00
0x00 5385		DAC_SR	DAC status register	0x00
0x00 5386 to 0x00 5387		Reserved area (2 bytes)		
0x00 5388		DAC_RDHRH	DAC right aligned data holding register high	0x00
0x00 5389		DAC_RDHRL	DAC right aligned data holding register low	0x00
0x00 538A to 0x00 538B		Reserved area (2 bytes)		
0x00 538C		DAC_LDHRH	DAC left aligned data holding register high	0x00
0x00 538D		DAC_LDHRL	DAC left aligned data holding register low	0x00
0x00 538E to 0x00 538F		Reserved area (2 bytes)		
0x00 5390		DAC_DHR8	DAC 8-bit data holding register	0x00
0x00 5391 to 0x00 53AB		Reserved area (27 bytes)		
0x00 53AC		DAC_DORH	DAC data output register high	0x00
0x00 53AD		DAC_DORL	DAC data output register low	0x00
0x00 53AE to 0x00 53FF	Reserved area (82 bytes)			

7 Option bytes

Option bytes contain configurations for device hardware features as well as the memory protection of the device. They are stored in a dedicated memory block.

All option bytes can be modified in ICP mode (with SWIM) by accessing the EEPROM address. See *Table 12* for details on option byte addresses.

The option bytes can also be modified 'on the fly' by the application in IAP mode, except for the ROP and UBC values which can only be taken into account when they are modified in ICP mode (with the SWIM).

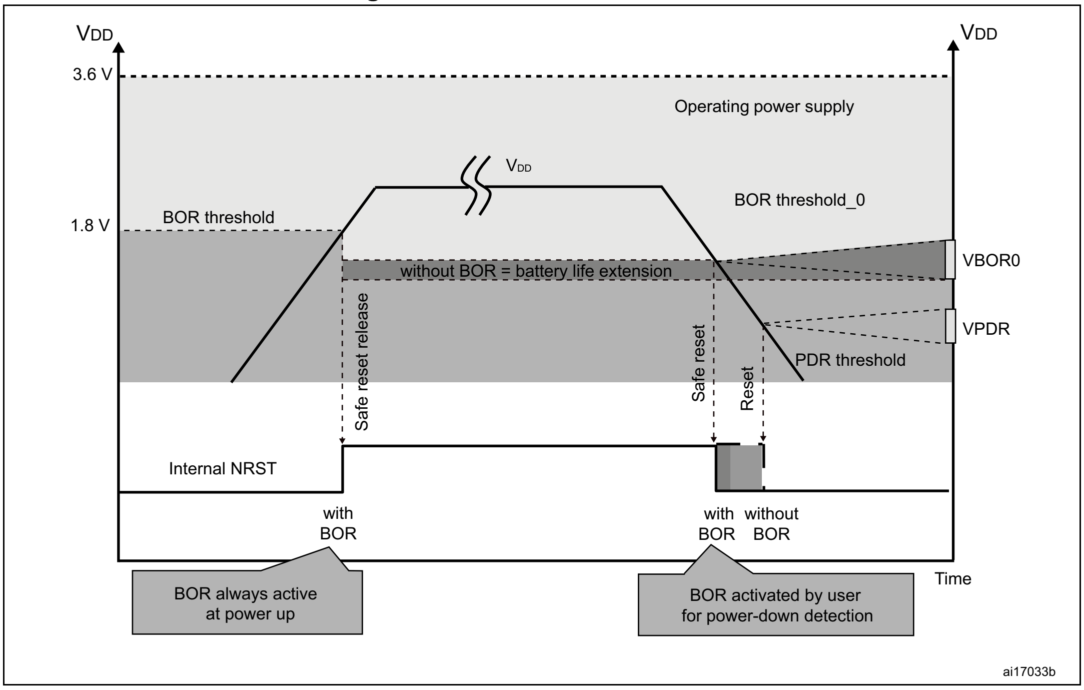
Refer to the STM8L15x Flash programming manual (PM0054) and STM8 SWIM and Debug Manual (UM0470) for information on SWIM programming procedures.

Table 12. Option byte addresses

Addr.	Option name	Option byte No.	Option bits								Factory default setting
			7	6	5	4	3	2	1	0	
0x00 4800	Read-out protection (ROP)	OPT0	ROP[7:0]								0xAA
0x00 4802	UBC (User Boot code size)	OPT1	UBC[7:0]								0x00
0x00 4807	Reserved										0x00
0x00 4808	Independent watchdog option	OPT3 [3:0]	Reserved				WWDG _HALT	WWDG _HW	IWDG _HALT	IWDG _HW	0x00
0x00 4809	Number of stabilization clock cycles for HSE and LSE oscillators	OPT4	Reserved				LSECNT[1:0]		HSECNT[1:0]		0x00
0x00 480A	Brownout reset (BOR)	OPT5 [3:0]	Reserved				BOR_TH			BOR_ ON	0x00
0x00 480B	Bootloader option bytes (OPTBL)	OPTBL [15:0]	OPTBL[15:0]								0x00
0x00 480C											0x00

1. Data guaranteed by design.
2. Data based on characterization results.

Figure 12. POR/BOR thresholds



9.3.3 Supply current characteristics

Total current consumption

The MCU is placed under the following conditions:

- All I/O pins in input mode with a static value at V_{DD} or V_{SS} (no load)
- All peripherals are disabled except if explicitly mentioned.

In the following table, data is based on characterization results, unless otherwise specified.

Subject to general operating conditions for V_{DD} and T_A.

Figure 15. Typ. $I_{DD(LPR)}$ vs. V_{DD} (LSI clock source)

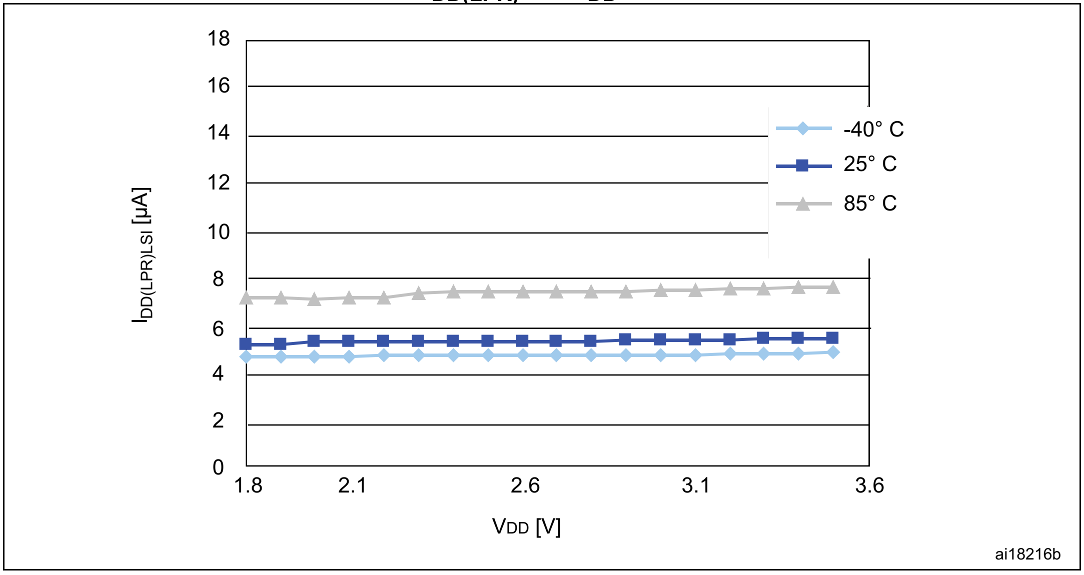


Figure 16. Typ. $I_{DD(LPW)}$ vs. V_{DD} (LSI clock source)

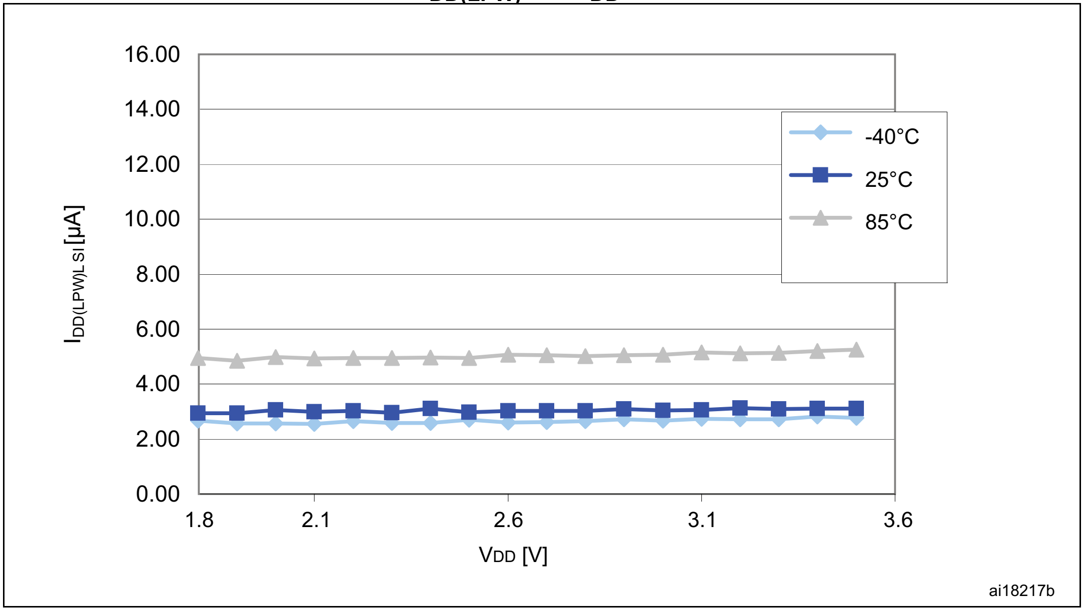


Table 24. Total current consumption and timing in Active-halt mode at V_{DD} = 1.65 V to 3.6 V

Symbol	Parameter	Conditions [(1)]			Typ	Max	Unit
$I_{DD(AH)}$	Supply current in Active-halt mode	LSE external clock (32.768 kHz) [(6)]	LCD OFF[(7)]	T_A = -40 °C to 25 °C	0.5	1.2	µA
				T_A = 55 °C	0.62	1.4	
				T_A = 85 °C	0.88	2.1	
				T_A = 105 °C	2.1	4.85	
				T_A = 125 °C	4.8	11	
			LCD ON (static duty/ external V_{LCD}) [(3)]	T_A = -40 °C to 25 °C	0.85	1.9	
				T_A = 55 °C	0.95	2.2	
				T_A = 85 °C	1.3	3.2	
				T_A = 105 °C	2.3	5.3	
				T_A = 125 °C	5.0	12	
			LCD ON (1/4 duty/ external V_{LCD}) [(4)]	T_A = -40 °C to 25 °C	1.5	2.5	
				T_A = 55 °C	1.6	3.8	
				T_A = 85 °C	1.8	4.2	
				T_A = 105 °C	2.9	7.0	
				T_A = 125 °C	5.7	14	
			LCD ON (1/4 duty/ internal V_{LCD}) [(5)]	T_A = -40 °C to 25 °C	3.4	7.6	
				T_A = 55 °C	3.7	8.3	
				T_A = 85 °C	3.9	9.2	
				T_A = 105 °C	5.0	14.5	
				T_A = 125 °C	6.3	15.2	
$I_{DD(WUFAH)}$	Supply current during wakeup time from Active-halt mode (using HSI)	-		-	2.4	-	mA
$t_{WU\_HSI(AH)}$ [(8)(9)]	Wakeup time from Active-halt mode to Run mode (using HSI)	-		-	4.7	7	µs
$t_{WU\_LSI(AH)}$ [(8)(9)]	Wakeup time from Active-halt mode to Run mode (using LSI)	-		-	150	-	µs

1. No floating I/O, unless otherwise specified.
2. RTC enabled. Clock source = LSI
3. RTC enabled, LCD enabled with external V_{LCD} = 3 V, static duty, division ratio = 256, all pixels active, no LCD connected.
4. RTC enabled, LCD enabled with external V_{LCD}, 1/4 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
5. LCD enabled with internal LCD booster V_{LCD} = 3 V, 1/4 duty, 1/3 bias, division ratio = 64, all pixels active, no LCD connected.
6. Oscillator bypassed (LSEBYP = 1 in CLK_ECKCR). When configured for external crystal, the LSE consumption ($I_{DD\ LSE}$) must be added. Refer to Table 32.
7. RTC enabled. Clock source = LSE.
8. Wakeup time until start of interrupt vector fetch.
   The first word of interrupt routine is fetched 4 CPU cycles after t_{WU}.
9. ULP=0 or ULP=1 and FWU=1 in the PWR_CSR2 register.

9.3.5 Memory characteristics

T_A = -40 to 125 °C unless otherwise specified.

Table 35. RAM and hardware registers

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RM}	Data retention mode (1)	Halt mode (or Reset)	1.65	-	-	V

1. Minimum supply voltage without losing data stored in RAM (in Halt mode or under Reset) or in hardware registers (only in Halt mode). Guaranteed by characterization, not tested in production.

Flash memory

Table 36. Flash program and data EEPROM memory

Symbol	Parameter	Conditions	Min	Typ	Max (1)	Unit
V_{DD}	Operating voltage (all modes, read/write/erase)	f_{SYSCLK} = 16 MHz	1.65	-	3.6	V
t_{prog}	Programming time for 1 or 64 bytes (block) erase/write cycles (on programmed byte)	-	-	6	-	ms
	Programming time for 1 to 64 bytes (block) write cycles (on erased byte)	-	-	3	-	ms
I_{prog}	Programming/ erasing consumption	T_A=+25 °C, V_{DD} = 3.0 V	-	0.7	-	mA
		T_A=+25 °C, V_{DD} = 1.8 V	-	0.7	-	
t_{RET}(2)	Data retention (program memory) after 10000 erase/write cycles at T_A= –40 to +85 °C (6 suffix)	T_{RET} = +85 °C	30(1)	-	-	years
	Data retention (program memory) after 10000 erase/write cycles at T_A= –40 to +125 °C (3 suffix)	T_{RET} = +125 °C	5(1)	-	-	
	Data retention (data memory) after 300000 erase/write cycles at T_A= –40 to +85 °C (6 suffix)	T_{RET} = +85 °C	30(1)	-	-	
	Data retention (data memory) after 300000 erase/write cycles at T_A= –40 to +125 °C (3 suffix)	T_{RET} = +125 °C	5(1)	-	-	
N_{RW} (3)	Erase/write cycles (program memory)	T_A = –40 to +85 °C (6 suffix), T_A = –40 to +125 °C (3 suffix)	10(1)	-	-	kcycles
	Erase/write cycles (data memory)		300(1) (4)	-	-	

1. Data based on characterization results.
2. Conforming to JEDEC JESD22a117
3. The physical granularity of the memory is 4 bytes, so cycling is performed on 4 bytes even when a write/erase operation addresses a single byte.
4. Data based on characterization performed on the whole data memory.

9.3.6 I/O current injection characteristics

As a general rule, current injection to the I/O pins, due to external voltage below V_{SS} or above V_{DD} (for standard pins) should be avoided during normal product operation. However, in order to give an indication of the robustness of the microcontroller in cases when abnormal injection accidentally happens, susceptibility tests are performed on a sample basis during device characterization.

Functional susceptibility to I/O current injection

While a simple application is executed on the device, the device is stressed by injecting current into the I/O pins programmed in floating input mode. While current is injected into the I/O pin, one at a time, the device is checked for functional failures.

The failure is indicated by an out of range parameter: ADC error, out of spec current injection on adjacent pins or other functional failure (for example reset, oscillator frequency deviation, LCD levels, etc.).

The test results are given in the following table.

Table 37. I/O current injection susceptibility

Symbol	Description	Functional susceptibility		Unit
		Negative injection	Positive injection	
I_{INJ}	Injected current on true open-drain pins (PC0 and PC1)	-5	+0	mA
	Injected current on all five-volt tolerant (FT) pins	-5	+0	
	Injected current on all 3.6 V tolerant (TT) pins	-5	+0	
	Injected current on any other pin	-5	+5	

9.3.7 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified. All unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor.

6. R_{PU} pull-up equivalent resistor based on a resistive transistor (corresponding I_{PU} current characteristics described in *Figure 24*).

Figure 21. Typical V_{IL} and V_{IH} vs V_{DD} (high sink I/Os)

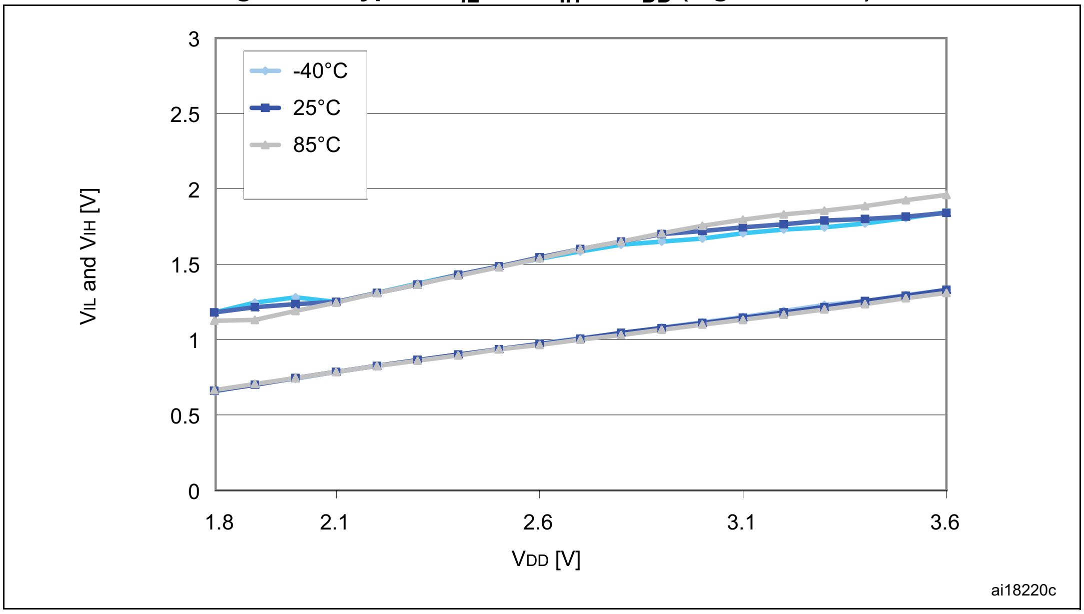


Figure 22. Typical V_{IL} and V_{IH} vs V_{DD} (true open drain I/Os)

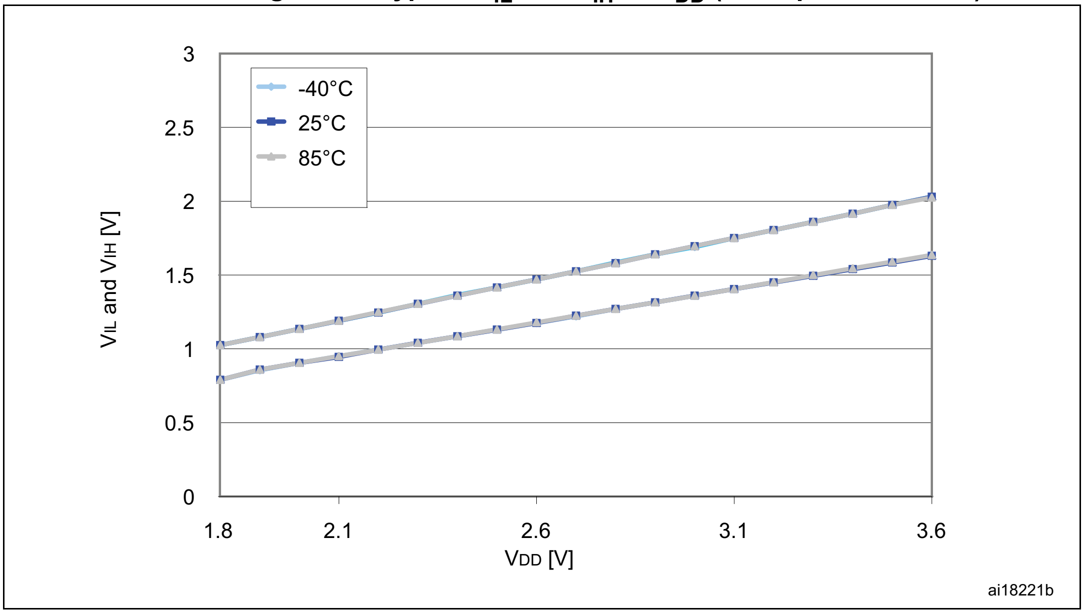
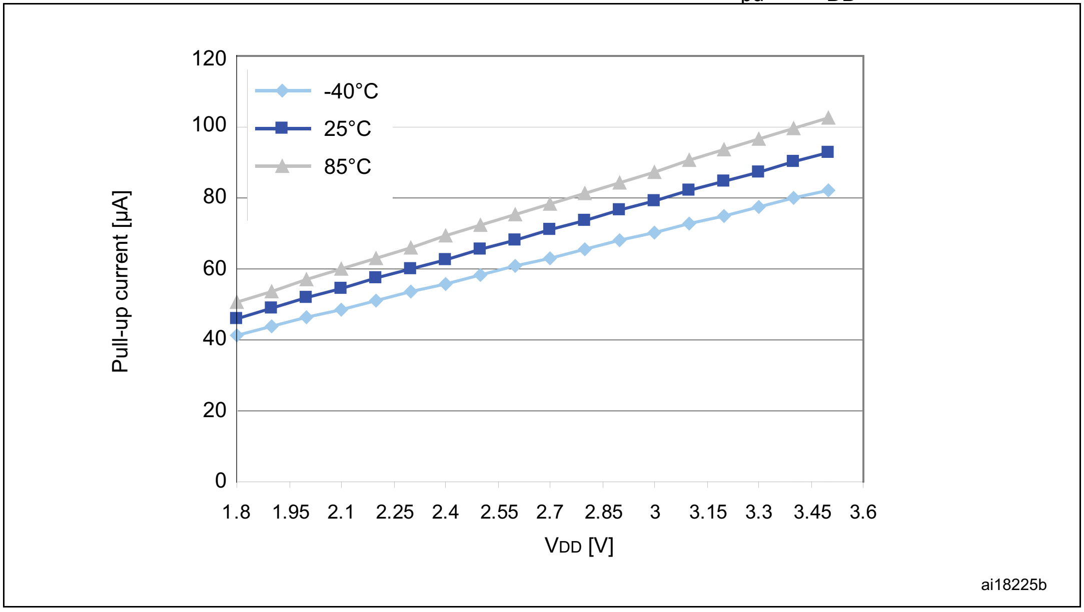


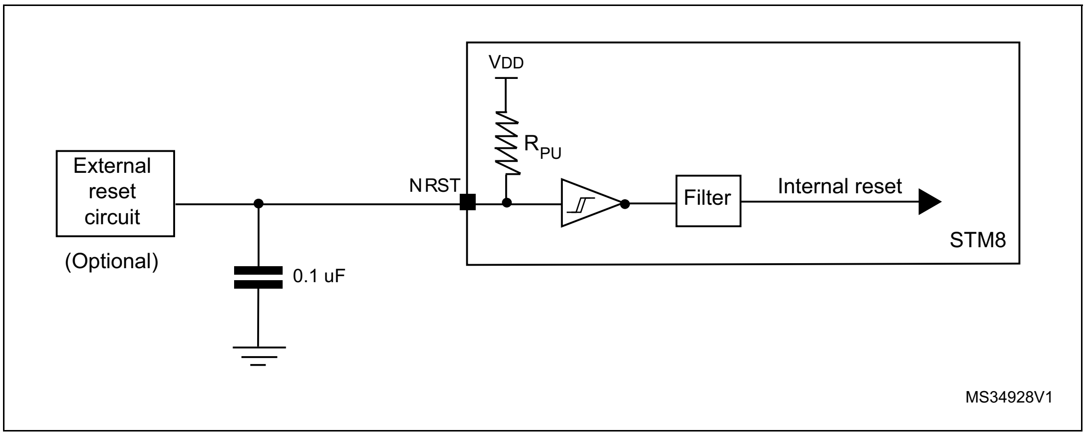
Figure 32. Typical NRST pull-up current I_{pu} vs V_{DD}



The reset network shown in *Figure 33* protects the device against parasitic resets. The user must ensure that the level on the NRST pin can go below the $V_{IL(NRST)}$ max. level specified in *Table 42*. Otherwise the reset is not taken into account internally.

For power consumption sensitive applications, the external reset capacitor value can be reduced to limit the charge/discharge current. If the NRST signal is used to reset the external circuitry, attention must be paid to the charge/discharge time of the external capacitor to fulfill the external devices reset timing conditions. The minimum recommended capacity is 10 nF.

Figure 33. Recommended NRST pin configuration



9.3.8 Communication interfaces

SPI1 - Serial peripheral interface

Unless otherwise specified, the parameters given in Table 43 are derived from tests performed under ambient temperature, f_{SYSCLK} frequency and V_{DD} supply voltage conditions summarized in Section 9.3.1. Refer to I/O port characteristics for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO).

Table 43. SPI1 characteristics

Symbol	Parameter	Conditions[1]	Min	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI1 clock frequency	Master mode	0	8	MHz
		Slave mode	0	8	
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI1 clock rise and fall time	Capacitive load: C = 30 pF	-	30	ns
$t_{su(NSS)}$[2]	NSS setup time	Slave mode	4 x $1/f_{SYSCLK}$	-	
$t_{h(NSS)}$[2]	NSS hold time	Slave mode	80	-	
$t_{w(SCKH)}$[2] $t_{w(SCKL)}$[2]	SCK high and low time	Master mode, f_{MASTER} = 8 MHz, f_{SCK}= 4 MHz	105	145	
$t_{su(MI)}$[2] $t_{su(SI)}$[2]	Data input setup time	Master mode	30	-	
		Slave mode	3	-	
$t_{h(MI)}$[2] $t_{h(SI)}$[2]	Data input hold time	Master mode	15	-	
		Slave mode	0	-	
$t_{a(SO)}$[2][3]	Data output access time	Slave mode	-	3x $1/f_{SYSCLK}$	
$t_{dis(SO)}$[2][4]	Data output disable time	Slave mode	30	-	
$t_{v(SO)}$[2]	Data output valid time	Slave mode (after enable edge)	-	60	
$t_{v(MO)}$[2]	Data output valid time	Master mode (after enable edge)	-	20	
$t_{h(SO)}$[2]	Data output hold time	Slave mode (after enable edge)	15	-	
$t_{h(MO)}$[2]		Master mode (after enable edge)	1	-	

1. Parameters are given by selecting 10 MHz I/O output frequency.
2. Values based on design simulation and/or characterization results.
3. Min time is for the minimum time to drive the output and max time is for the maximum time to validate the data.
4. Min time is for the minimum time to invalidate the output and max time is for the maximum time to put the data in Hi-Z.

Figure 38. ADC1 accuracy characteristics

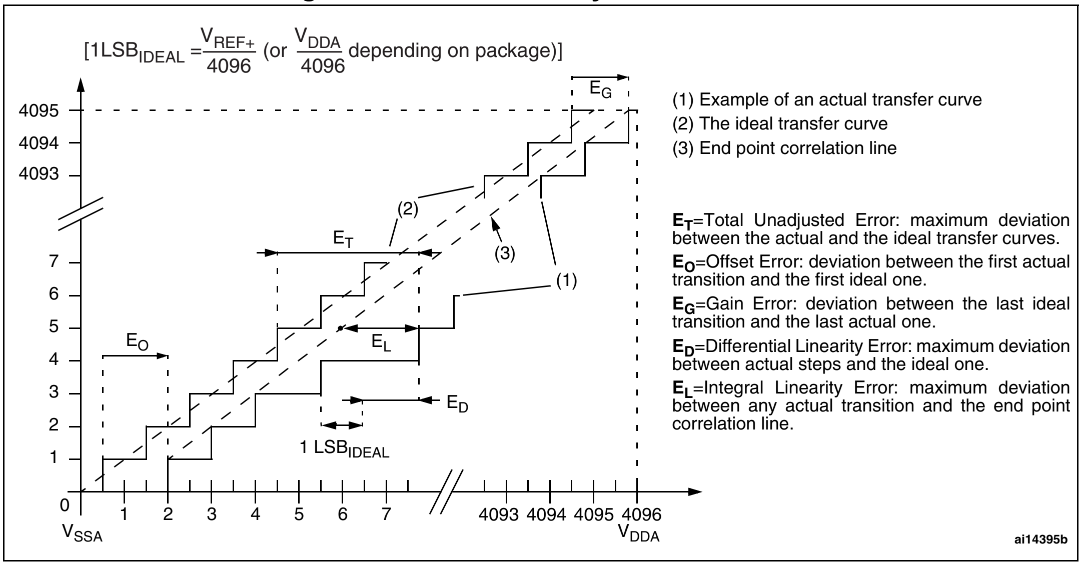
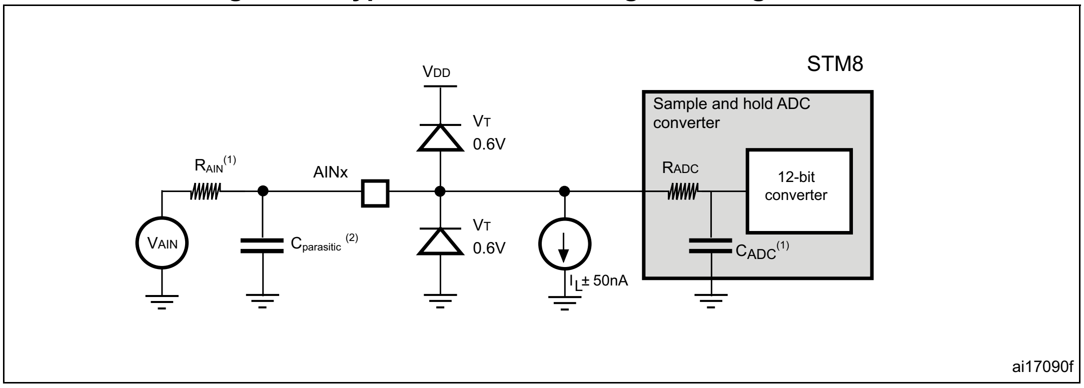


Figure 39. Typical connection diagram using the ADC



1. Refer to *Table 53* for the values of R_{AIN} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

9.3.15 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 61000 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 61000 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 58. EMS data

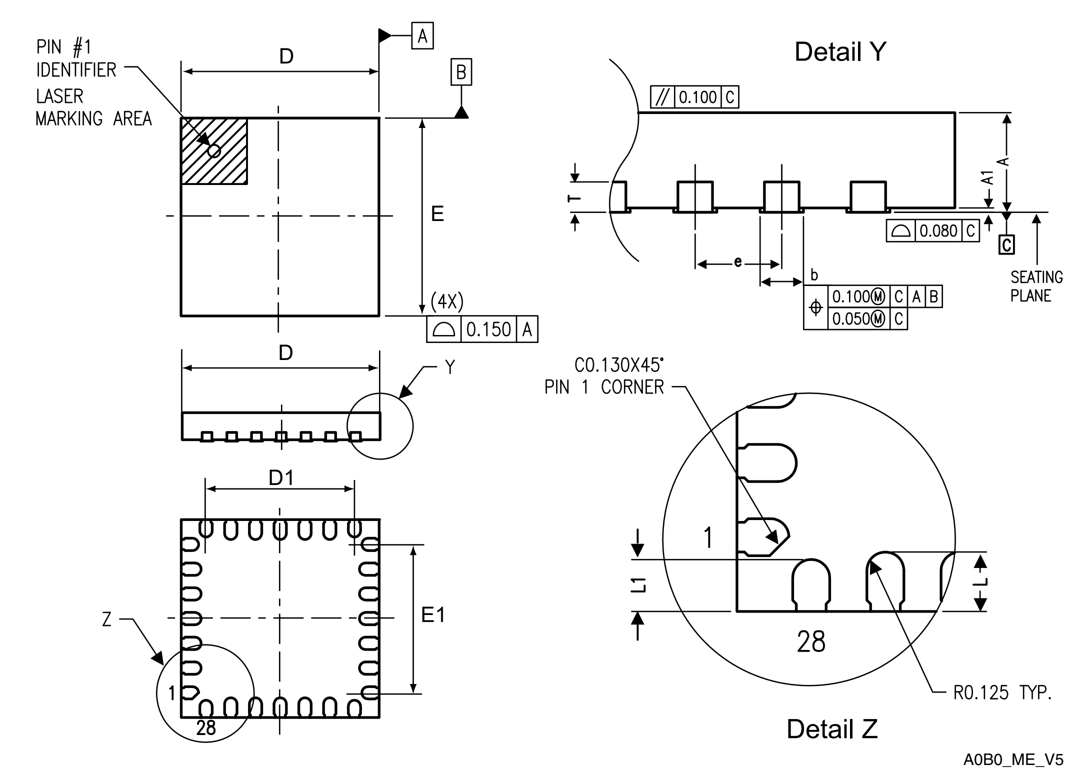
Symbol	Parameter	Conditions		Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU}= 16 MHz, conforms to IEC 61000		3B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, T_A = +25 °C, f_{CPU} = 16 MHz, conforms to IEC 61000	Using HSI	4A
			Using HSE	2B

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC61967-2 which specifies the board and the loading of each pin.

10.6 UFQFPN28 package information

Figure 55. UFQFPN28 - 28-lead, 4 x 4 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline



1. Drawing is not to scale.

Table 66. UFQFPN28 - 28-lead, 4 x 4 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package mechanical data(1)

Symbol	millimeters			inches		
	Min	Typ	Max	Min	Typ	Max
A	0.500	0.550	0.600	0.0197	0.0217	0.0236
A1	-	0.000	0.050	-	0.0000	0.0020
D	3.900	4.000	4.100	0.1535	0.1575	0.1614
D1	2.900	3.000	3.100	0.1142	0.1181	0.1220
E	3.900	4.000	4.100	0.1535	0.1575	0.1614
E1	2.900	3.000	3.100	0.1142	0.1181	0.1220
L	0.300	0.400	0.500	0.0118	0.0157	0.0197
L1	0.250	0.350	0.450	0.0098	0.0138	0.0177
T	-	0.152	-	-	0.0060	-
b	0.200	0.250	0.300	0.0079	0.0098	0.0118
e	-	0.500	-	-	0.0197	-

Table 67. WLCSP28 - 28-pin, 1.703 x 2.841 mm, 0.4 mm pitch wafer level chip scale package mechanical data

Symbol	millimeters			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	0.540	0.570	0.600	0.0213	0.0224	0.0236
A1	-	0.190	-	-	0.0075	-
A2	-	0.380	-	-	0.0150	-
b(2)	0.240	0.270	0.300	0.0094	0.0106	0.0118
D	1.668	1.703	1.738	0.0657	0.0670	0.0684
E	2.806	2.841	2.876	0.1105	0.1119	0.1132
e	-	0.400	-	-	0.0157	-
e1	-	1.200	-	-	0.0472	-
e2	-	2.400	-	-	0.0945	-
F	-	0.251	-	-	0.0099	-
G	-	0.222	-	-	0.0087	-
aaa	-	-	0.100	-	-	0.0039
bbb	-	-	0.100	-	-	0.0039
ccc	-	-	0.100	-	-	0.0039
ddd	-	-	0.050	-	-	0.0020
eee	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Dimension is measured at the maximum bump diameter parallel to primary datum Z.

Device marking

The following figure gives an example of topside marking orientation versus ball A1 identifier location. Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.